

$V_{DSS}$	1200V
$R_{DS(on)}$ (Typ.)	105mΩ
$I_D^{*1}$	24A
$P_D$	134W

### ●Features

- 1) Qualified to AEC-Q101
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Fast reverse recovery
- 5) Easy to parallel
- 6) Simple to drive
- 7) Pb-free lead plating ; RoHS compliant

### ●Application

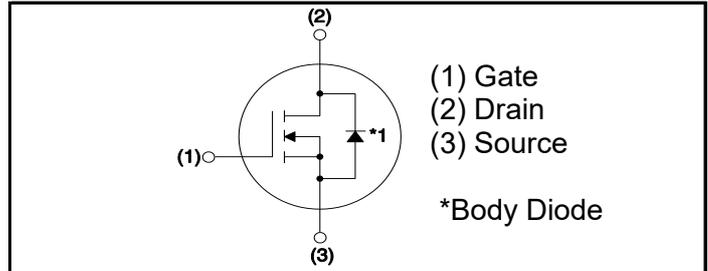
- Automobile
- Switch mode power supplies

### ●Outline

TO-247N



### ●Inner circuit



### ●Packaging specifications

Type	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	30
	Taping code	C11
	Marking	SCT3105KL

### ●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DSS}$	1200	V
Continuous Drain current	$T_c = 25^\circ\text{C}$	$I_D^{*1}$ 24	A
	$T_c = 100^\circ\text{C}$	$I_D^{*1}$ 17	A
Pulsed Drain current	$I_{D,pulse}^{*2}$	60	A
Gate - Source voltage (DC)	$V_{GSS}$	-4 to +22	V
Gate - Source surge voltage ( $t_{surge} < 300\text{nsec}$ )	$V_{GSS,surge}^{*3}$	-4 to +26	V
Recommended drive voltage	$V_{GS,op}^{*4}$	0 / +18	V
Junction temperature	$T_j$	175	$^\circ\text{C}$
Range of storage temperature	$T_{stg}$	-55 to +175	$^\circ\text{C}$

**●Electrical characteristics** ( $T_a = 25^\circ\text{C}$ )

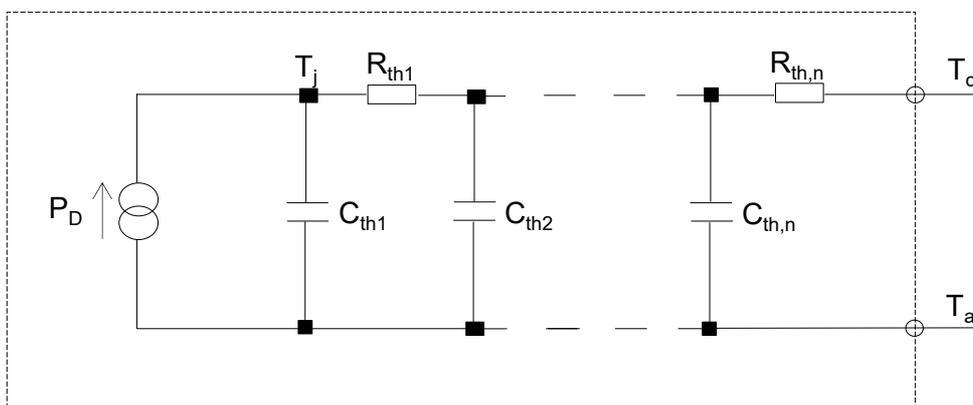
Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{V}$ , $I_D = 1\text{mA}$ $T_j = 25^\circ\text{C}$ $T_j = -55^\circ\text{C}$	1200 1200	- -	- -	V
Zero Gate voltage Drain current	$I_{DSS}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 1200\text{V}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	- -	1 2	10 -	$\mu\text{A}$
Gate - Source leakage current	$I_{GSS+}$	$V_{GS} = +22\text{V}$ , $V_{DS} = 0\text{V}$	-	-	100	nA
Gate - Source leakage current	$I_{GSS-}$	$V_{GS} = -4\text{V}$ , $V_{DS} = 0\text{V}$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10\text{V}$ , $I_D = 3.81\text{mA}$	2.7	-	5.6	V
Static Drain - Source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = 18\text{V}$ , $I_D = 7.6\text{A}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	- -	105 179	137 -	$\text{m}\Omega$
Gate input resistance	$R_G$	$f = 1\text{MHz}$ , open drain	-	13	-	$\Omega$

**●Thermal resistance**

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	$R_{thJC}$	-	0.86	1.12	$^\circ\text{C}/\text{W}$

**●Typical Transient Thermal Characteristics**

Symbol	Value	Unit	Symbol	Value	Unit
$R_{th1}$	1.08E-01	K/W	$C_{th1}$	4.72E-04	Ws/K
$R_{th2}$	3.73E-01		$C_{th2}$	3.97E-03	
$R_{th3}$	3.41E-01		$C_{th3}$	1.31E-02	



●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	$g_{fs}^{*5}$	V <sub>DS</sub> = 10V, I <sub>D</sub> = 7.6A	-	3.4	-	S
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	574	-	pF
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 800V	-	59	-	
Reverse transfer capacitance	C <sub>riss</sub>	f = 1MHz	-	28	-	
Effective output capacitance, energy related	C <sub>o(er)</sub>	V <sub>GS</sub> = 0V V <sub>DS</sub> = 0V to 600V	-	159	-	pF
Total Gate charge	Q <sub>g</sub> <sup>*5</sup>	V <sub>DS</sub> = 600V I <sub>D</sub> = 7.6A	-	51	-	nC
Gate - Source charge	Q <sub>gs</sub> <sup>*5</sup>	V <sub>GS</sub> = 18V	-	10	-	
Gate - Drain charge	Q <sub>gd</sub> <sup>*5</sup>	See Fig. 1-1.	-	25	-	
Turn - on delay time	t <sub>d(on)</sub> <sup>*5</sup>	V <sub>DS</sub> = 400V I <sub>D</sub> = 7.6A	-	17	-	ns
Rise time	t <sub>r</sub> <sup>*5</sup>	V <sub>GS</sub> = 0V/+18V	-	27	-	
Turn - off delay time	t <sub>d(off)</sub> <sup>*5</sup>	R <sub>G</sub> = 0Ω R <sub>L</sub> = 53Ω	-	31	-	
Fall time	t <sub>f</sub> <sup>*5</sup>	See Fig. 1-1, 1-2.	-	17	-	
Turn - on switching loss	E <sub>on</sub> <sup>*5</sup>	V <sub>DS</sub> = 600V V <sub>GS</sub> =0V/18V, I <sub>D</sub> = 7.6A R <sub>G</sub> = 0Ω, L = 750μH	-	159	-	μJ
Turn - off switching loss	E <sub>off</sub> <sup>*5</sup>	E <sub>on</sub> includes diode reverse recovery L <sub>σ</sub> = 50nH, C <sub>σ</sub> = 200pF See Fig. 2-1, 2-2.	-	2	-	

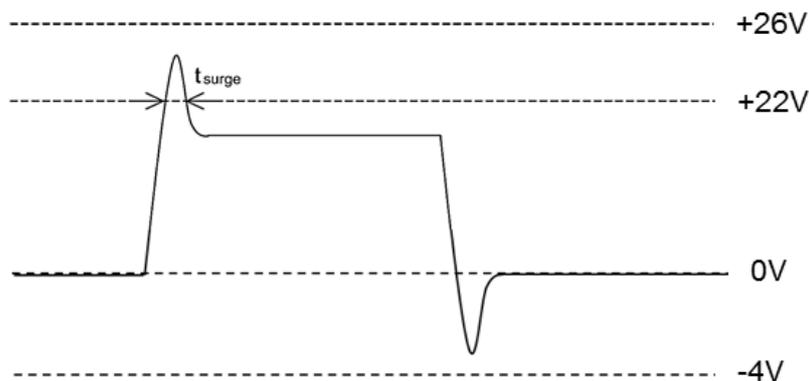
**●Body diode electrical characteristics (Source-Drain) ( $T_a = 25^\circ\text{C}$ )**

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous, forward current	$I_S$ *1	$T_c = 25^\circ\text{C}$	-	-	24	A
Body diode direct current, pulsed	$I_{SM}$ *2		-	-	60	A
Forward voltage	$V_{SD}$ *5	$V_{GS} = 0\text{V}, I_D = 7.6\text{A}$	-	3.2	-	V
Reverse recovery time	$t_{rr}$ *5	$I_F = 7.6\text{A}$ $V_R = 600\text{V}$ $di/dt = 1100\text{A}/\mu\text{s}$	-	15	-	ns
Reverse recovery charge	$Q_{rr}$ *5		-	53	-	nC
Peak reverse recovery current	$I_{rrm}$ *5		$L_\sigma = 50\text{nH}, C_\sigma = 200\text{pF}$ See Fig. 3-1, 3-2.	-	6.5	-

\*1 Limited by maximum temperature allowed.

\*2  $P_W \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*3 Example of acceptable  $V_{GS}$  waveform



\*4 Please be advised not to use SiC-MOSFETs with  $V_{GS}$  below 13V as doing so may cause thermal runaway.

\*5 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

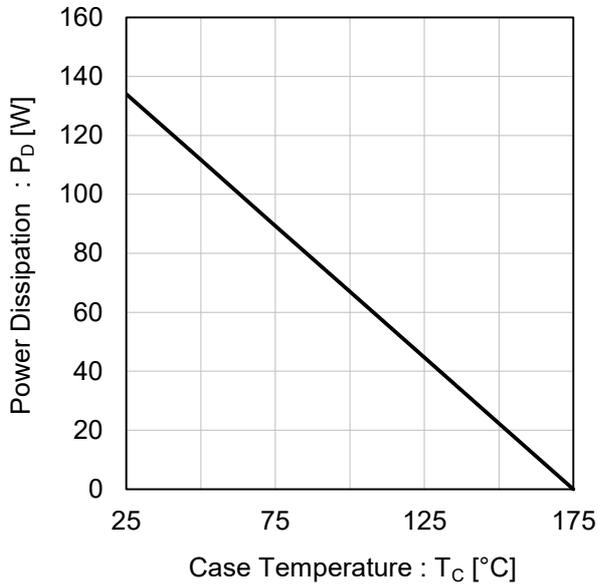


Fig.2 Maximum Safe Operating Area

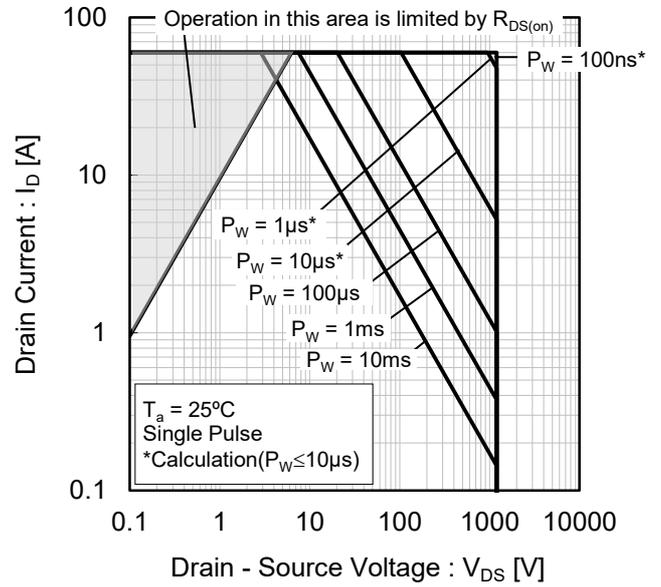
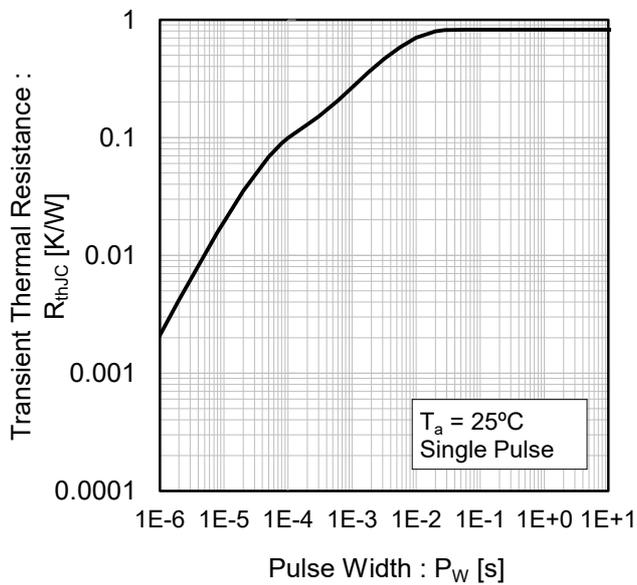


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

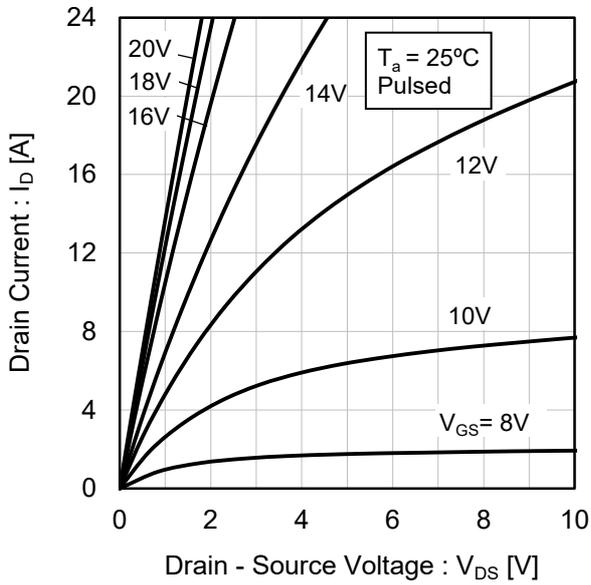


Fig.5 Typical Output Characteristics(II)

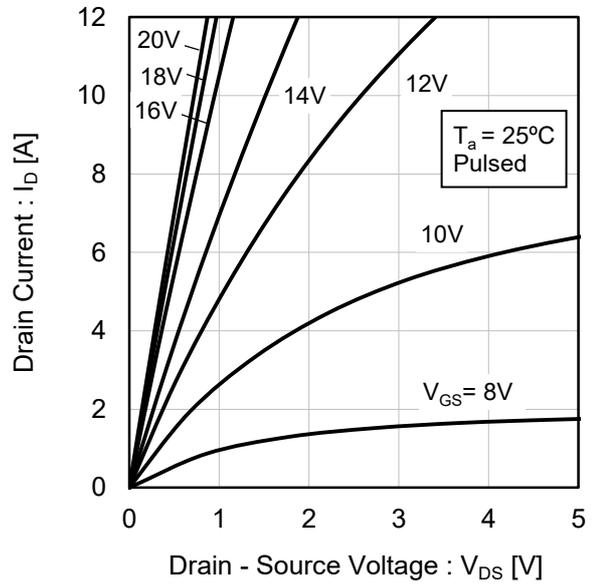
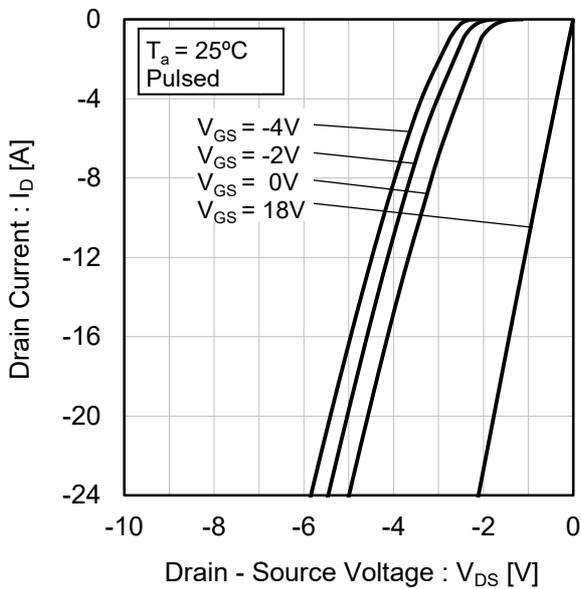


Fig.6  $T_j = 25^\circ\text{C}$  3rd Quadrant Characteristics



●Electrical characteristic curves

Fig.7  $T_j = 150^\circ\text{C}$  Typical Output Characteristics(I)

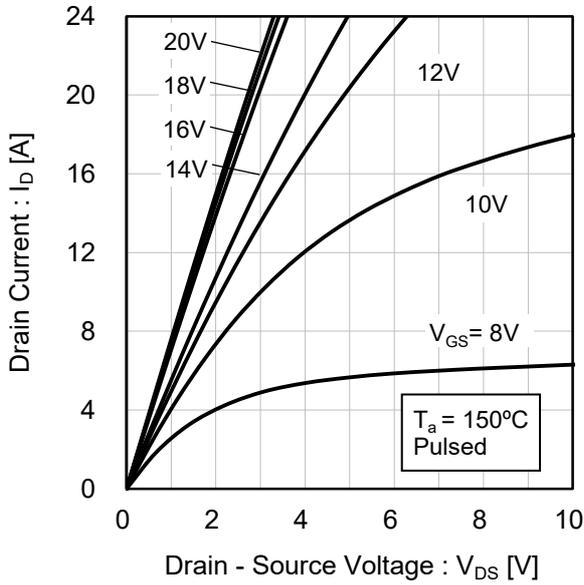


Fig.8  $T_j = 150^\circ\text{C}$  Typical Output Characteristics(II)

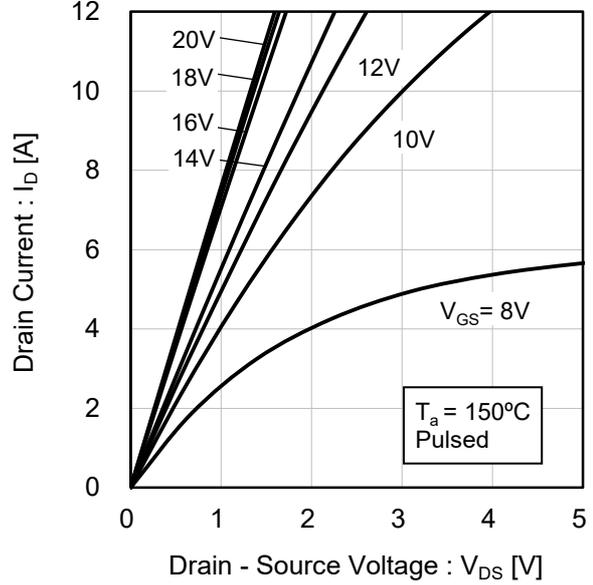


Fig.9  $T_j = 150^\circ\text{C}$  3rd Quadrant Characteristics

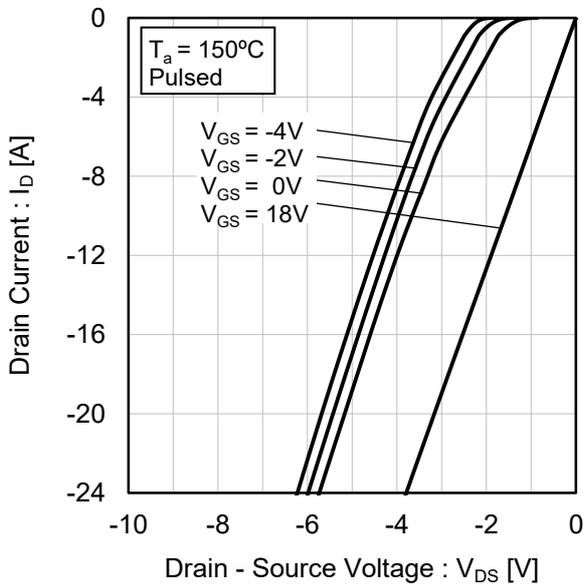
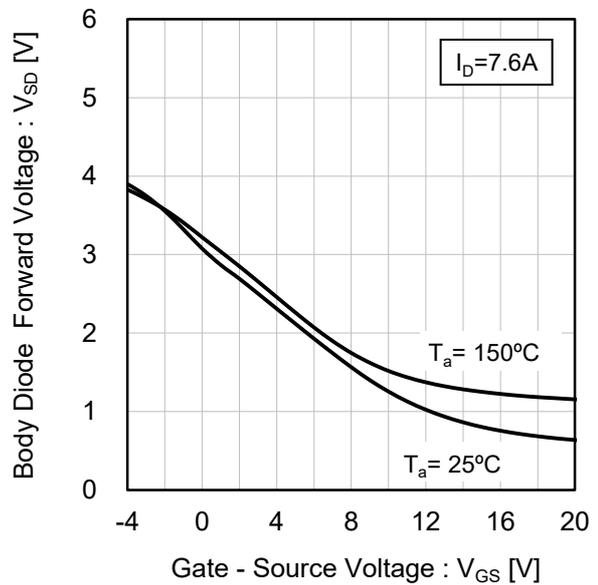


Fig.10 Body Diode Forward Voltage vs. Gate - Source Voltage



●Electrical characteristic curves

Fig.11 Typical Transfer Characteristics (I)

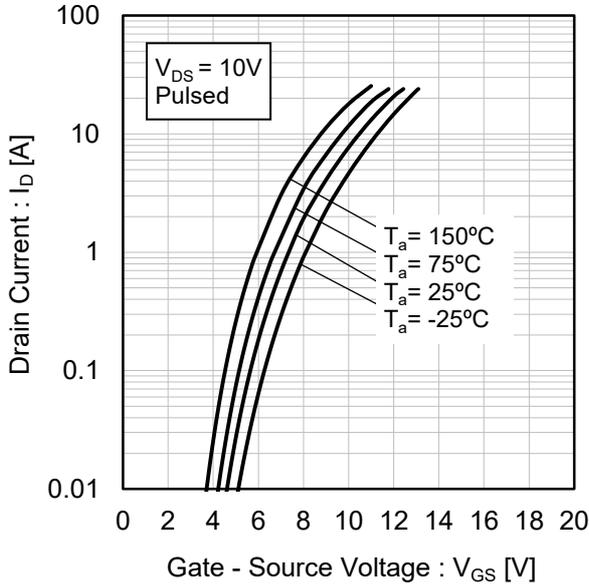


Fig.12 Typical Transfer Characteristics (II)

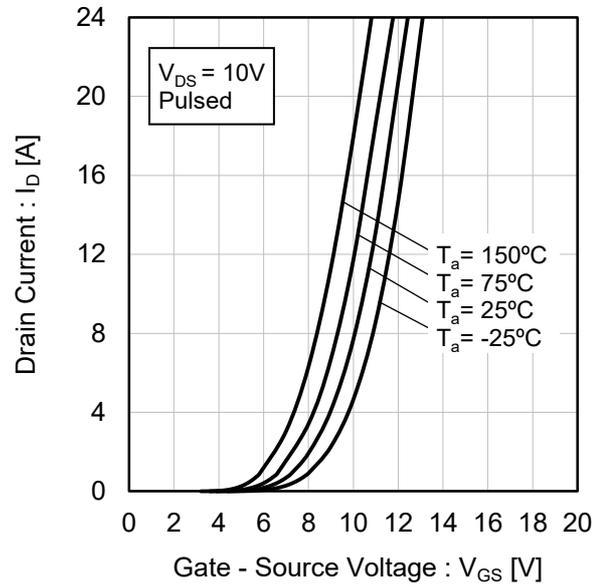


Fig.13 Gate Threshold Voltage vs. Junction Temperature

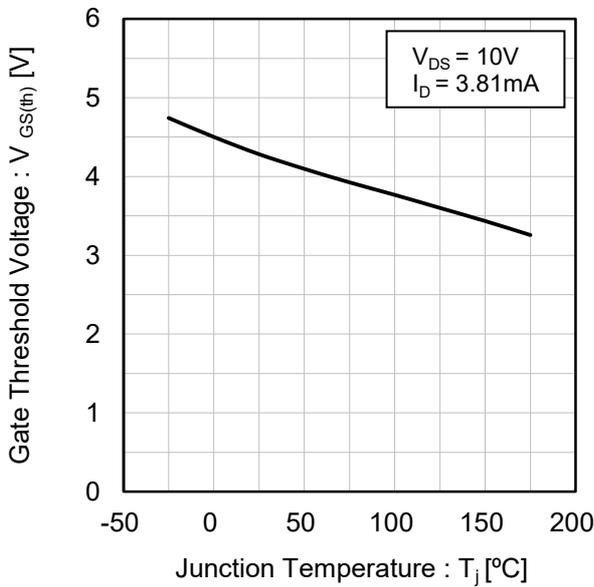
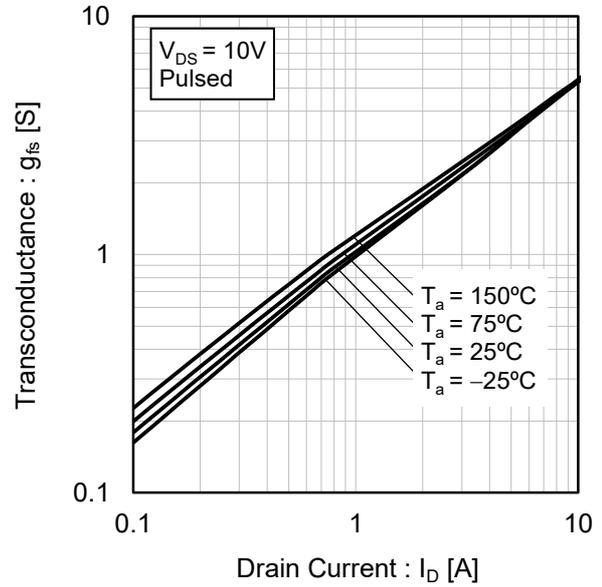


Fig.14 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

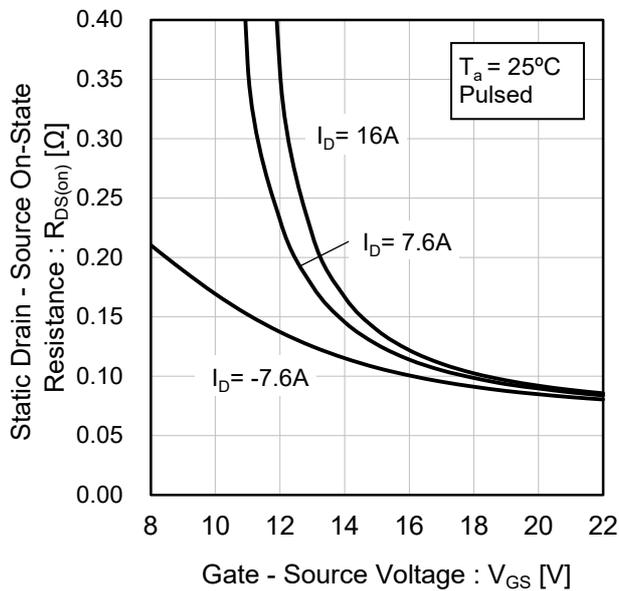


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

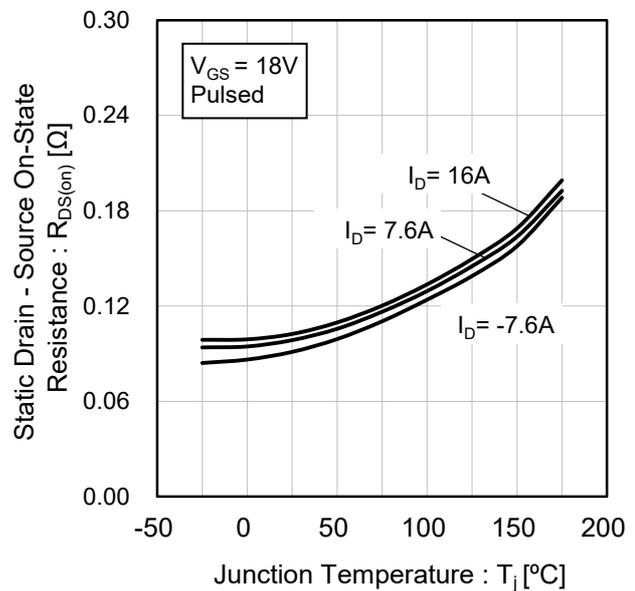


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current

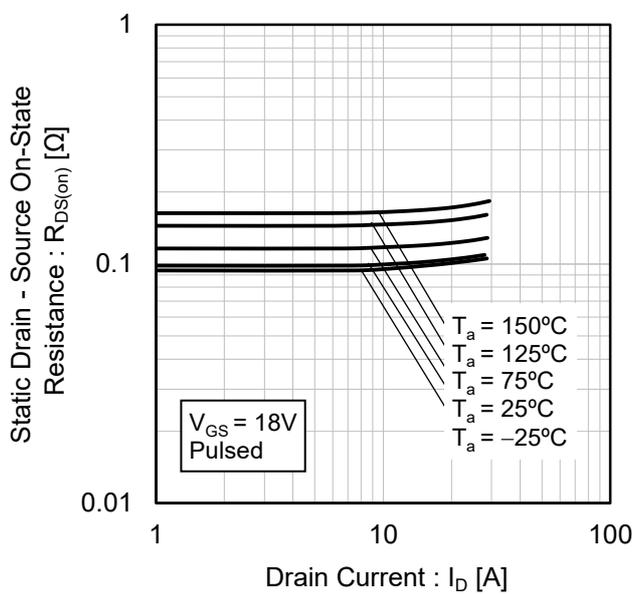
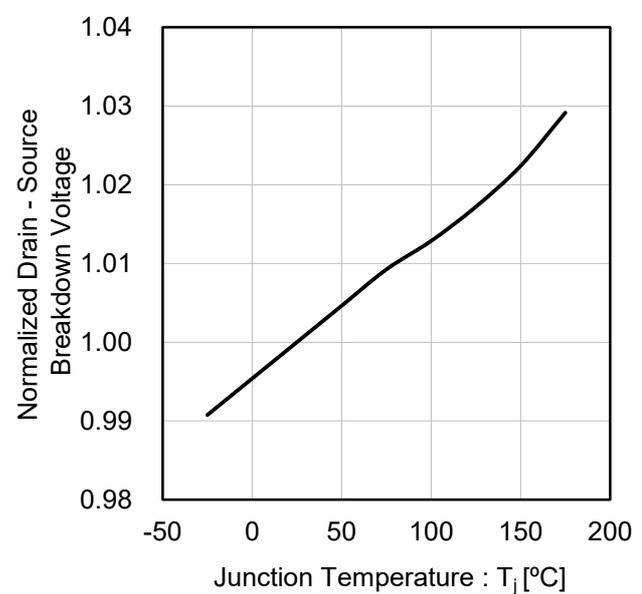


Fig.18 Normalized Drain - Source Breakdown Voltage vs. Junction Temperature



●Electrical characteristic curves

Fig.19 Typical Capacitance vs. Drain - Source Voltage

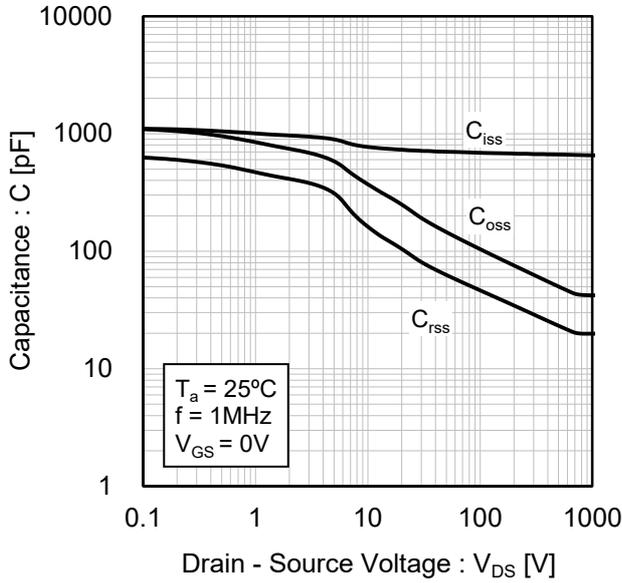


Fig.20  $C_{oss}$  Stored Energy

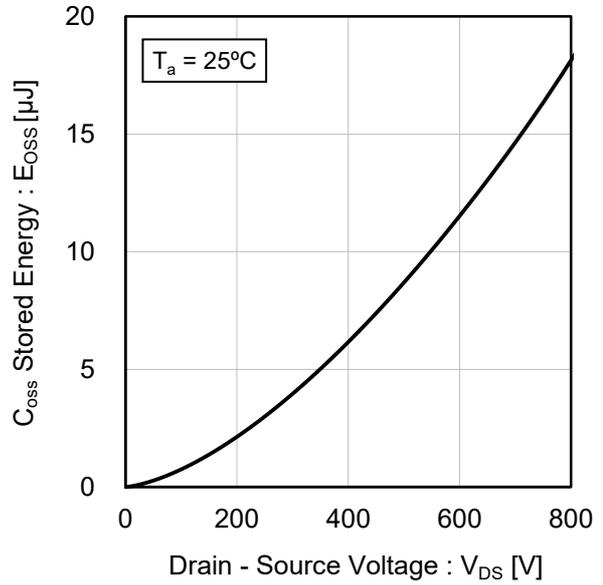
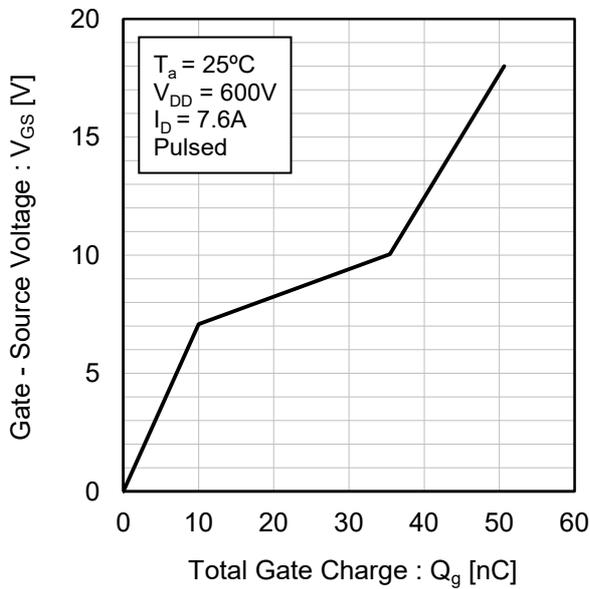
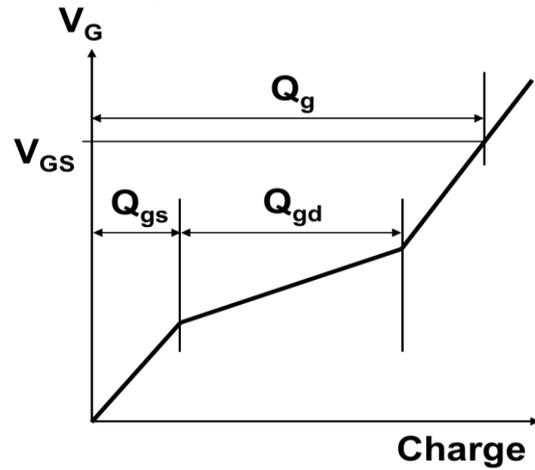


Fig.21 Dynamic Input Characteristics



\*Gate Charge Waveform



●Electrical characteristic curves

Fig.19 Typical Switching Time vs. Drain Current

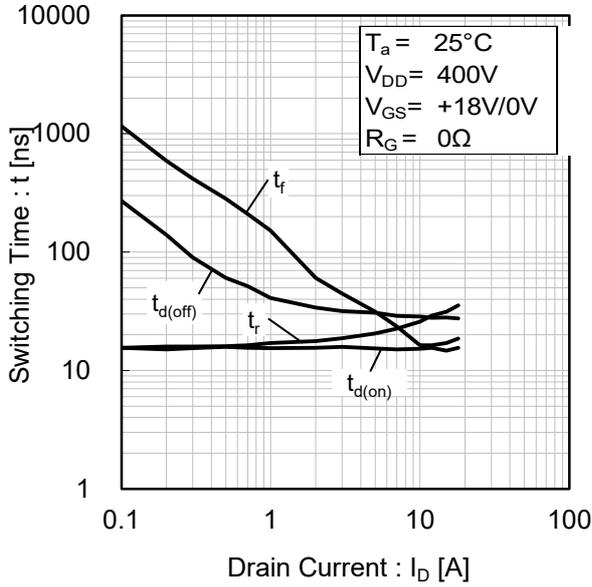


Fig.20 Typical Switching Loss vs. Drain - Source Voltage

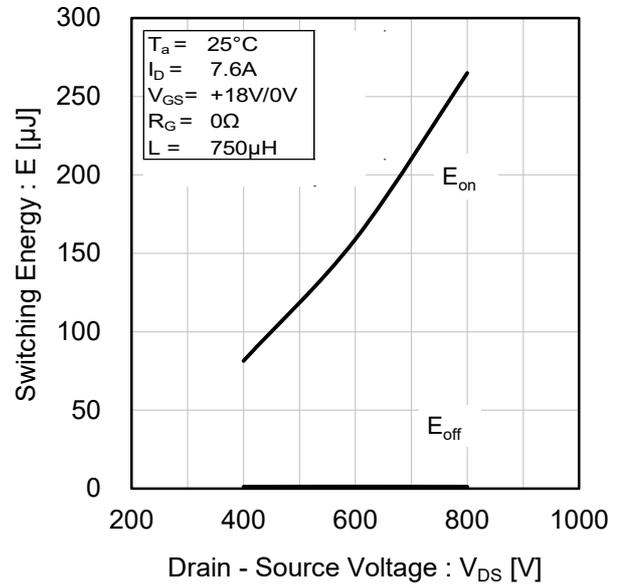


Fig.21 Typical Switching Loss vs. Drain Current

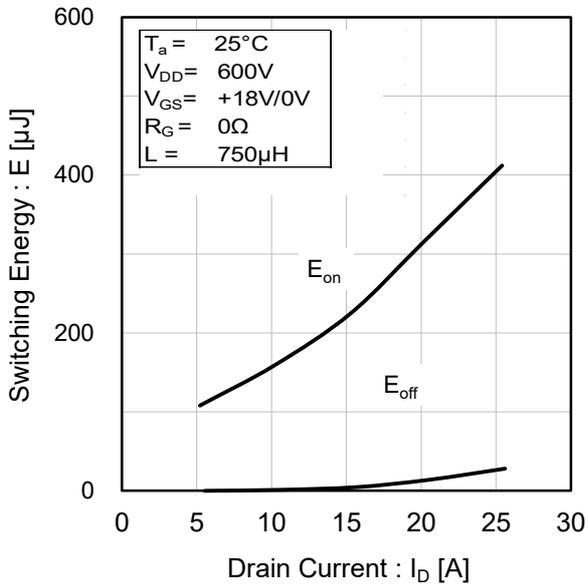
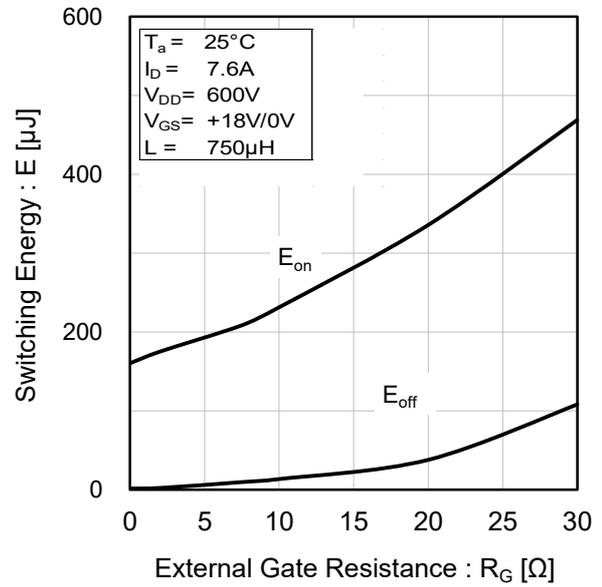


Fig.22 Typical Switching Loss vs. External Gate Resistance



● Measurement circuits and waveforms

Fig.1-1 Gate Charge and Switching Time Measurement Circuit

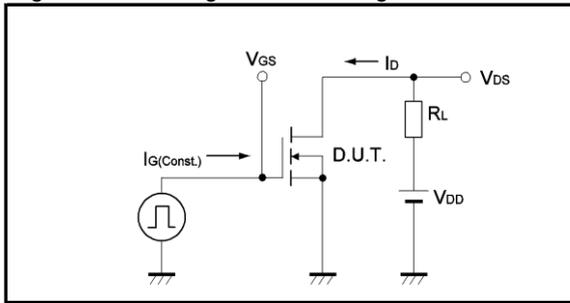


Fig.1-2 Waveforms for Switching Time

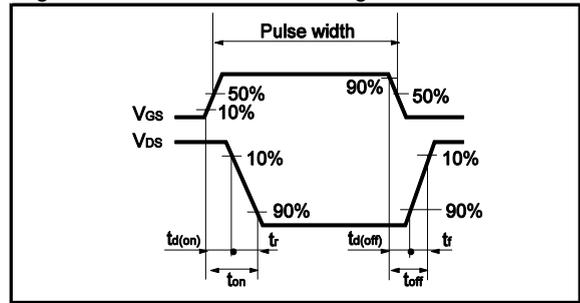


Fig.2-1 Switching Energy Measurement Circuit

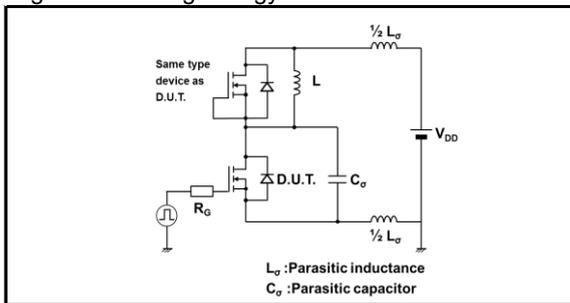


Fig.2-2 Waveforms for Switching Energy Loss

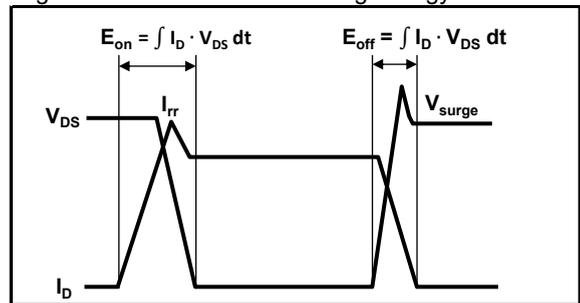


Fig.3-1 Reverse Recovery Time Measurement Circuit

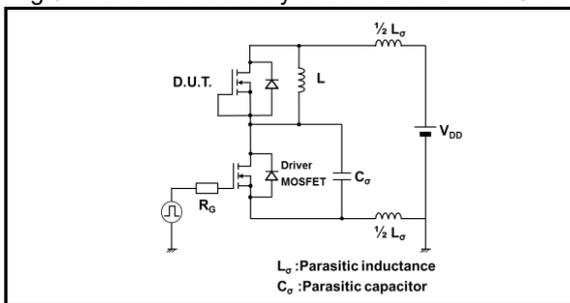
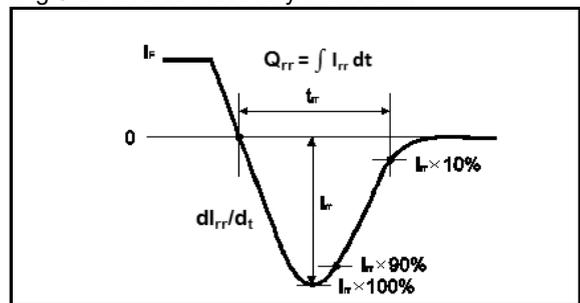


Fig.3-2 Reverse Recovery Waveform



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